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Perpendicular switching of a single ferromagnetic layer induced by in-plane current injection

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[1] I. M. Miron, K. Garello, G. Gaudin, P.-J. Zermatten, M. V. Costache, S. Auffret, S. Bandera, B. Rodmacq, A. Schuhl, and P. Gambardella, *Nature* 476, 189 (2011). Kevin Garello, Catalan Institute of Nanotechnology (ICN-CIN2), E-08193 Barcelona, Spain